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## A 24-32 GHz single-chip harmonic balance power amplifier for 5G MW application

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## **Abstract:**

This article introduces the CM output-matching networks in the Balance architecture and discusses the theory and design process of a broadband RF-input Class-F PA balanced power amplifier. The harmonic balance network ensures the operation of second and third-harmonic and determines output impedance for wideband response. The input MN is considered as a band-pass filter. The reactance is taken from IMN. It stabilized the operation the design. The suggested HBPA's results show an output power of up to 30.9 dBm, more peak power-added efficiency (PAE) of 35.6% at 27 GHz, and a small signal gain of less than 28.6 dB. Over the 24–30 GHz range, saturated output power (Psat) and uniform gain are both reached with variations of less than 0.8 dB.

## **Keywords:**

Harmonic Balance Power Amplifier, GaN HEMT, LDMOS, power-added efficiency (PAE)